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74HC1G126; 74HCT1G126

Bus buffer/line driver; 3-state

Rev. 04 — 20 July 2007

Product data sheet

1. General description

The 74HC1G126 and 74HCT1G126 are high-speed, Si-gate CMOS devices. They provide one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input pin (OE). A LOW at pin OE causes the output as assume a high-impedance OFF-state.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The bus driver output currents are equal to those of the 74HC126 and 74HCT126.

2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC1G126GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1
74HCT1G126GW			body width 1.25 mm	
74HC1G126GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74HCT1G126GV				

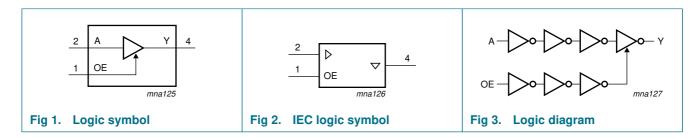
4. Marking

Table 2. Marking codes

Type number	Marking
74HC1G126GW	HN
74HCT1G126GW	TN
74HC1G126GV	H26
74HCT1G126GV	T26

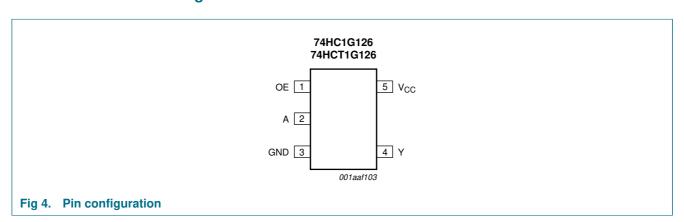


5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
OE	1	output enable input
Α	2	data input
GND	3	ground (0 V)
Υ	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table

 $H = HIGH \ voltage \ level; \ L = LOW \ voltage \ level; \ X = don't \ care; \ Z = high-impedance \ OFF-state$

Inputs		Output
OE	A	Υ
Н	L	L
Н	Н	Н
L	X	Z

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±35.0	mA
I _{CC}	supply current		-	70	mA
I_{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[2]</u> _	200	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	ibol Parameter Conditions		74HC1G126		74HCT1G126			Unit	
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 \text{ V}$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	mbol Parameter Conditions		-40	–40 °C to +85 °C			–40 °C to +125 °C		
			Min	Тур	Max	Min	Max		
For type 7	74HC1G126								
V_{IH}	V _{IH} HIGH-level input voltage	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	V	
		$V_{CC} = 4.5 \text{ V}$	3.15	2.4	-	3.15	-	V	
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	V	
V_{IL}	LOW-level input	$V_{CC} = 2.0 \text{ V}$	-	8.0	0.5	-	0.5	V	
voltage	voltage	$V_{CC} = 4.5 \text{ V}$	-	2.1	1.35	-	1.35	V	
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	V	

^[2] Above 55 $^{\circ}$ C the value of Ptot derates linearly with 2.5 mW/K.

 Table 7.
 Static characteristics ... continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

$V_{OH} \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	- - - -	V V V
voltage $\begin{split} I_O = -20~\mu\text{A}; ~V_{CC} = 2.0~V & 1.9 & 2.0 & - & 1.9 \\ I_O = -20~\mu\text{A}; ~V_{CC} = 4.5~V & 4.4 & 4.5 & - & 4.4 \\ I_O = -20~\mu\text{A}; ~V_{CC} = 6.0~V & 5.9 & 6.0 & - & 5.9 \\ I_O = -6.0~\text{mA}; ~V_{CC} = 4.5~V & 3.84 & 4.32 & - & 3.7 \end{split}$	-	V
$I_{O} = -20 \mu\text{A}; V_{CC} = 4.5 \text{V} \qquad 4.4 \qquad 4.5 \qquad - \qquad 4.4$ $I_{O} = -20 \mu\text{A}; V_{CC} = 6.0 \text{V} \qquad 5.9 \qquad 6.0 \qquad - \qquad 5.9$ $I_{O} = -6.0 \text{mA}; V_{CC} = 4.5 \text{V} \qquad 3.84 \qquad 4.32 \qquad - \qquad 3.7$	-	V
$I_{O} = -20 \mu\text{A}; V_{CC} = 6.0 \text{V}$ 5.9 6.0 - 5.9 $I_{O} = -6.0 \text{mA}; V_{CC} = 4.5 \text{V}$ 3.84 4.32 - 3.7	-	
$I_O = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$ 3.84 4.32 - 3.7	-	V
	-	
$I_O = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$ 5.34 5.81 - 5.2		V
	-	V
V_{OL} LOW-level output $V_{I} = V_{IH}$ or V_{IL}		
voltage $I_{O} = 20 \mu A; V_{CC} = 2.0 V$ - 0 0.1 -	0.1	V
$I_O = 20 \mu A; V_{CC} = 4.5 V$ - 0 0.1 -	0.1	V
$I_O = 20 \ \mu A; \ V_{CC} = 6.0 \ V$ - 0 0.1 -	0.1	V
$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$ - 0.15 0.33 -	0.4	V
$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$ - 0.16 0.33 -	0.4	V
I_I input leakage current $V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$ - 1.0	1.0	μΑ
I_{OZ} OFF-state output $V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or 5 - current GND; $V_{CC} = 6.0 \text{ V}$	10	μΑ
I_{CC} supply current $V_I = V_{CC}$ or GND; $I_O = 0$ A; - 10 - $V_{CC} = 6.0 \text{ V}$	20	μΑ
C _I input capacitance - 1.5	-	pF
For type 74HCT1G126		
V_{IH} HIGH-level input $V_{CC} = 4.5 \text{ V}$ to 5.5 V 2.0 1.6 - 2.0 voltage	-	V
V_{IL} LOW-level input $V_{CC} = 4.5 \text{ V}$ to 5.5 V - $1.2 0.8$ - voltage	8.0	V
V_{OH} HIGH-level output $V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$		
voltage $I_0 = -20 \mu\text{A}$ 4.4 4.5 - 4.4	-	V
$I_{O} = -6.0 \text{ mA}$ 3.84 4.32 - 3.7	-	V
V_{OL} LOW-level output $V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$		
voltage $I_0 = 20 \mu\text{A}$ - 0 0.1 -	0.1	V
$I_{O} = 6.0 \text{ mA}$ - 0.16 0.33 -	0.4	V
I_I input leakage current $V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$ - 1.0	1.0	μΑ
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	10	
I_{CC} supply current $V_I = V_{CC}$ or GND; $I_O = 0$ A; - 10 - $V_{CC} = 5.5 \text{ V}$	20	μΑ
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	850	μΑ
C _I input capacitance - 1.5	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

 $GND = 0 \ V; t_r = t_f \le 6.0 \ ns; C_L = 50 \ pF$ unless otherwise specified. All typical values are measured at $T_{amb} = 25 \ ^{\circ}C$. For test circuit see Figure 7

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	-40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	
For type	74HC1G126								•
t _{pd}	propagation delay	A to Y; see Figure 5	[1]						
		V _{CC} = 2.0 V		-	24	125	-	150	ns
		$V_{CC} = 4.5 \text{ V}$		-	10	25	-	30	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	9	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$		-	9	21	-	26	ns
t _{en}	enable time	OE to Y; see Figure 6	[1]						
		$V_{CC} = 2.0 \text{ V}$		-	24	155	-	190	ns
		$V_{CC} = 4.5 \text{ V}$		-	10	31	-	38	ns
		$V_{CC} = 6.0 \text{ V}$		-	8	26	-	32	ns
t _{dis}	disable time	OE to Y; see Figure 6	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}$		-	16	155	-	190	ns
		$V_{CC} = 4.5 \text{ V}$		-	12	31	-	38	ns
		$V_{CC} = 6.0 \text{ V}$		-	11	26	-	32	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[2]	-	30	-	-	-	pF
For type	74HCT1G126								
t _{pd}	propagation delay	A to Y; see Figure 5	[1]						
		V _{CC} = 4.5 V		-	11	30	-	36	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	10	-	-	-	ns
t _{en}	enable time	OE to Y; see Figure 6; V _{CC} = 4.5 V	[1]	-	10	35	-	42	ns
t _{dis}	disable time	OE to Y; see Figure 6; V _{CC} = 4.5 V	[1]	-	12	31	-	38	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to $V_{CC} - 1.5 V$	[2]	-	27	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

ten is the same as tPZL and tPZH.

 $t_{\mbox{\scriptsize dis}}$ is the same as $t_{\mbox{\scriptsize PLZ}}$ and $t_{\mbox{\scriptsize PHZ}}.$

[2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz

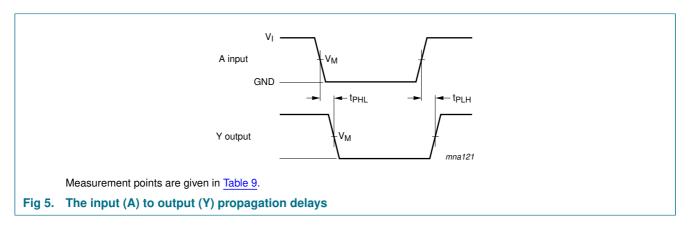
fo = output frequency in MHz

 C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs}$

12. Waveforms



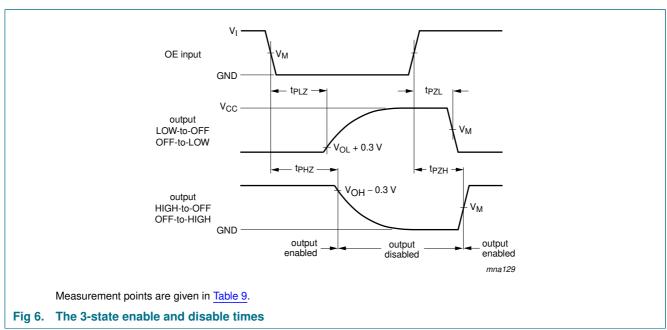
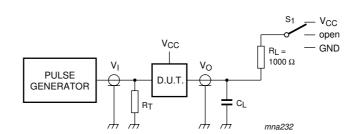


Table 9. Measurement points

Туре	Input	Output	
	V _M	V _I	V _M
74HC1G126	$0.5 \times V_{CC}$	GND to V _{CC}	$0.5 \times V_{CC}$
74HCT1G126	1.3 V	GND to 3.0 V	1.3 V



Test data is given in Table 8. Definitions for test circuit:

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator

 C_L = Load capacitance including jig and probe capacitance

R_L = Load resistance

For t_{PLH} , t_{PHL} , $S_1 = open$

For t_{PLZ} , t_{PZL} , $S_1 = V_{CC}$

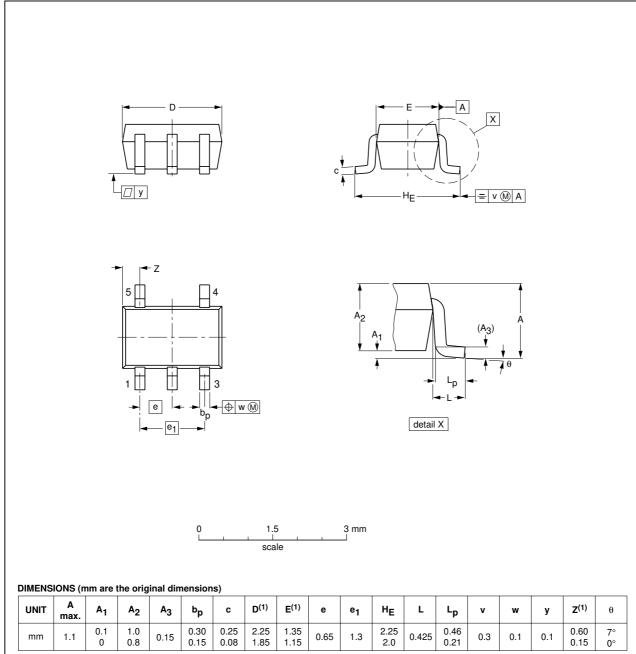
For t_{PHZ} , t_{PZH} , $S_1 = GND$

Fig 7. Load circuitry for switching times

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A			00-09-01 03-02-19

Fig 8. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

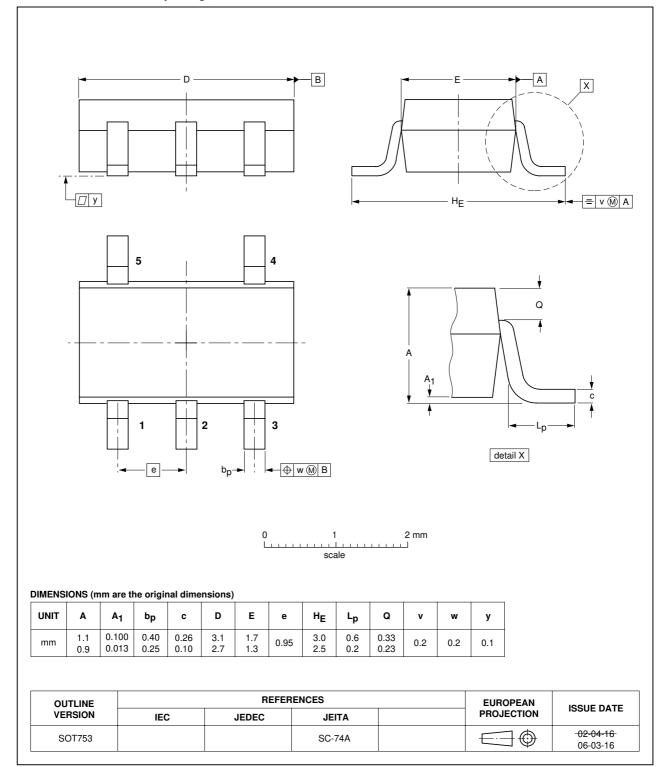


Fig 9. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 10. Abbreviations

Acronym	Description
DUT	Device Under Test
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Release date	Data sheet status	Change notice	Supersedes	
20070720	Product data sheet	-	74HC_HCT1G126_3	
 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
 Legal texts have been adapted to the new company name where appropriate. 				
 Package SOT353 changed to SOT353-1 in <u>Table 1</u> and <u>Figure 8</u>. 				
 Quick Reference Data and Soldering sections removed. 				
Section 2 "Features" updated.				
20020515	Product specification	-	74HC_HCT1G126_2	
20010406	Product specification	-	74HC_HCT1G126	
19970924	Preliminary specification	-	-	
	20070720 • The formation guidelines of the second	 20070720 Product data sheet The format of this data sheet has been reguidelines of NXP Semiconductors. Legal texts have been adapted to the new Package SOT353 changed to SOT353-1 if Quick Reference Data and Soldering sect Section 2 "Features" updated. 20020515 Product specification 20010406 Product specification 	20070720 Product data sheet • The format of this data sheet has been redesigned to comply viguidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where the package SOT353 changed to SOT353-1 in Table 1 and Figure to Quick Reference Data and Soldering sections removed. • Section 2 "Features" updated. 20020515 Product specification -	

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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